

# **Voltage Regulator** - Low **Power Low, Dropout** 100 mA

# LP2950, LP2951, NCV2951

The LP2950 and LP2951 are micropower voltage regulators that are specifically designed to maintain proper regulation with an extremely low input-to-output voltage differential. These devices feature a very low quiescent bias current of 75 µA and are capable of supplying output currents in excess of 100 mA. Internal current and thermal limiting protection is provided.

The LP2951 has three additional features. The first is the  $\overline{\text{Error}}$ Output that can be used to signal external circuitry of an out of regulation condition, or as a microprocessor power-on reset. The second feature allows the output voltage to be preset to 5.0 V, 3.3 V or 3.0 V output (depending on the version) or programmed from 1.25 V to 29 V. It consists of a pinned out resistor divider along with direct access to the Error Amplifier feedback input. The third feature is a Shutdown input that allows a logic level signal to turn-off or turn-on the regulator output.

Due to the low input-to-output voltage differential and bias current specifications, these devices are ideally suited for battery powered computer, consumer, and industrial equipment where an extension of useful battery life is desirable. The LP2950 is available in the three pin case 29 and DPAK packages, and the LP2951 is available in the eight pin dual-in-line, SOIC-8 and Micro8 surface mount packages. The 'A' suffix devices feature an initial output voltage tolerance  $\pm 0.5\%$ .

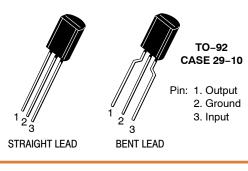
#### **Features**

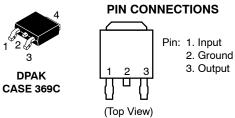
- Low Quiescent Bias Current of 75 μA
- Low Input-to-Output Voltage Differential of 50 mV at 100 μA and 380 mV at 100 mA
- 5.0 V, 3.3 V or 3.0 V  $\pm 0.5\%$  Allows Use as a Regulator or Reference
- Extremely Tight Line and Load Regulation
- Requires Only a 1.0 μF Output Capacitor for Stability
- Internal Current and Thermal Limiting
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and RoHS Compliant

#### LP2951 Additional Features

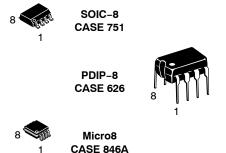
- Error Output Signals an Out of Regulation Condition
- Output Programmable from 1.25 V to 29 V
- Logic Level Shutdown Input

(See Following Page for Device Information.)

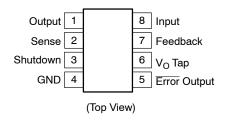




Heatsink surface (shown as terminal 4 in case outline drawing) is connected to Pin 2.



## **PIN CONNECTIONS**



#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on pages 14 and 15 of this data sheet.

#### **DEVICE MARKING INFORMATION**

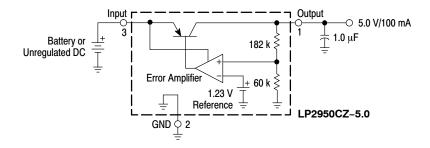
See general marking information in the device marking section on page 16 of this data sheet.

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#### **DEVICE INFORMATION**

		Output Voltage								
Package	3.0 V 3.3 V		5.0 V	Adjustable	Operating Ambient Temperature Range					
TO-92	LP2950CZ-3.0	LP2950CZ-3.3	LP2950CZ-5.0	Not	$T_A = -40^{\circ} \text{ to } +125^{\circ}\text{C}$					
Suffix Z	LP2950ACZ-3.0	LP2950ACZ-3.3	LP2950ACZ-5.0	Available						
DPAK	LP2950CDT-3.0	LP2950CDT-3.3	LP2950CDT-5.0	Not	$T_A = -40^{\circ} \text{ to } +125^{\circ}\text{C}$					
Suffix DT	LP2950ACDT-3.0	LP2950ACDT-3.3	LP2950ACDT-5.0	Available						
SOIC-8	-	NCV2951ACD-3.3R2	NCV2951ACDR2	NCV2951CDR2	$T_A = -40^{\circ} \text{ to } +125^{\circ}\text{C}$					
SOIC-8	LP2951CD-3.0	LP2951CD-3.3	LP2951CD	LP2951CD	$T_A = -40^{\circ} \text{ to } +125^{\circ}\text{C}$					
Suffix D	LP2951ACD-3.0	LP2951ACD-3.3	LP2951ACD	LP2951ACD						
Micro8	LP2951CDM-3.0	LP2951CDM-3.3	LP2951CDM	LP2951CDM	$T_A = -40^{\circ} \text{ to } +125^{\circ}\text{C}$					
Suffix DM	LP2951ACDM-3.0	LP2951ACDM-3.3	LP2951ACDM	LP2951ACDM						
DIP-8	LP2951CN-3.0	LP2951CN-3.3	LP2951CN	LP2951CN	$T_A = -40^{\circ} \text{ to } +125^{\circ}\text{C}$					
Suffix N	LP2951ACN-3.0	LP2951ACN-3.3	LP2951ACN	LP2951ACN						

LP2950Cx-xx / LP2951Cxx-xx LP2950ACx-xx / LP2951ACxx-xx 1% Output Voltage Precision at  $T_A$  = 25°C 0.5% Output Voltage Precision at  $T_A$  = 25°C



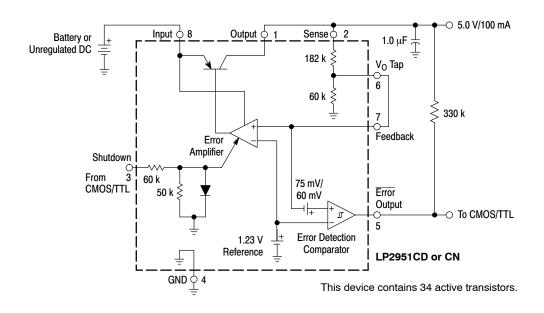


Figure 1. Representative Block Diagrams

# **MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$ , unless otherwise noted.)

Rating	Symbol	Value	Unit
Input Voltage	V <sub>CC</sub>	30	Vdc
Peak Transient Input Voltage (t < 300 ms)	V <sub>CC</sub>	32	Vdc
Power Dissipation and Thermal Characteristics			
Maximum Power Dissipation	$P_{D}$	Internally Limited	W
Case 751 (SOIC-8) D Suffix			
Thermal Resistance, Junction-to-Ambient	$R_{ hetaJA}$	180	°C/W
Thermal Resistance, Junction-to-Case	$R_{ hetaJC}$	45	°C/W
Case 369A (DPAK) DT Suffix (Note 1)			
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	92	°C/W
Thermal Resistance, Junction-to-Case	$R_{ hetaJC}$	6.0	°C/W
Case 29 (TO-226AA/TO-92) Z Suffix			
Thermal Resistance, Junction-to-Ambient	$R_{ hetaJA}$	160	°C/W
Thermal Resistance, Junction-to-Case	$R_{ hetaJC}$	83	°C/W
Case 626 N Suffix			
Thermal Resistance, Junction-to-Ambient	$R_{ hetaJA}$	105	°C/W
Case 846A (Micro8) DM Suffix			
Thermal Resistance, Junction-to-Ambient	$R_{ hetaJA}$	240	°C/W
Feedback Input Voltage	V <sub>fb</sub>	-1.5 to +30	Vdc
Shutdown Input Voltage	V <sub>sd</sub>	-0.3 to +30	Vdc
Error Comparator Output Voltage	V <sub>err</sub>	-0.3 to +30	Vdc
Operating Ambient Temperature Range	g Ambient Temperature Range $T_A$ -40 to +125		°C
Maximum Die Junction Temperature Range	TJ	+150	°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **ELECTRICAL CHARACTERISTICS**

 $(V_{in} = V_O + 1.0 \text{ V}, I_O = 100 \mu\text{A}, C_O = 1.0 \mu\text{F}, T_A = 25^{\circ}\text{C}$  [Note 3], unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Output Voltage, 5.0 V Versions	Vo				V
$V_{in} = 6.0 \text{ V}, I_{O} = 100 \mu\text{A}, T_{A} = 25^{\circ}\text{C}$					
LP2950C-5.0/LP2951C/NCV2951C*		4.950	5.000	5.050	
LP2950AC-5.0/LP2951AC/NCV2951AC*		4.975	5.000	5.025	
$T_A = -40 \text{ to } +125^{\circ}\text{C}$					
LP2950C-5.0/LP2951C/NCV2951C*		4.900	-	5.100	
LP2950AC-5.0/LP2951AC/NCV2951AC*		4.940	-	5.060	
$V_{in}$ = 6.0 to 30 V, $I_{O}$ = 100 $\mu A$ to 100 mA, $T_{A}$ = -40 to +125°C					
LP2950C-5.0/LP2951C/NCV2951C*		4.880	-	5.120	
LP2950AC-5.0/LP2951AC/NCV2951AC*		4.925	_	5.075	
Output Voltage, 3.3 V Versions	V <sub>O</sub>				V
$V_{in} = 4.3 \text{ V}, I_{O} = 100 \mu\text{A}, T_{A} = 25^{\circ}\text{C}$					
LP2950C-3.3/LP2951C-3.3		3.267	3.300	3.333	
LP2950AC-3.3/LP2951AC-3.3/NCV2951AC-3.3*		3.284	3.300	3.317	
$T_A = -40 \text{ to } +125^{\circ}\text{C}$					
LP2950C-3.3/LP2951C-3.3		3.234	-	3.366	
LP2950AC-3.3/LP2951AC-3.3/NCV2951AC-3.3*		3.260	-	3.340	
$V_{in}$ = 4.3 to 30 V, $I_{O}$ = 100 $\mu A$ to 100 mA, $T_{A}$ = -40 to +125°C					
LP2950C-3.3/LP2951C-3.3		3.221	-	3.379	
LP2950AC-3.3/LP2951AC-3.3/NCV2951AC-3.3*		3.254	-	3.346	
Output Voltage, 3.0 V Versions	V <sub>O</sub>				V
$V_{in}$ = 4.0 V, $I_{O}$ = 100 $\mu$ A, $T_{A}$ = 25°C					
LP2950C-3.0/LP2951C-3.0		2.970	3.000	3.030	
LP2950AC-3.0/LP2951AC-3.0		2.985	3.000	3.015	
$T_A = -40 \text{ to } +125^{\circ}\text{C}$					
LP2950C-3.0/LP2951C-3.0		2.940	-	3.060	
LP2950AC-3.0/LP2951AC-3.0		2.964	_	3.036	
$V_{in}$ = 4.0 to 30 V, $I_{O}$ = 100 $\mu A$ to 100 mA, $T_{A}$ = -40 to +125°C					
LP2950C-3.0/LP2951C-3.0		2.928	_	3.072	
LP2950AC-3.0/LP2951AC-3.0		2.958		3.042	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 1. The Junction-to-Ambient Thermal Resistance is determined by PCB copper area per Figure 29.
- 2. This device series contains ESD protection and exceeds the following tests:

Human Body Model (HBM), 2000 V, Class 2, JESD22 A114–C Machine Model (MM), 200 V, Class B, JESD22 A115–A

Charged Device Model (CDM), 2000 V, Class IV, JESD22 C101-C

- 3. Low duty pulse techniques are used during test to maintain junction temperature as close to ambient as possible.
- 4. V<sub>O(nom)</sub> is the part number voltage option.
- 5. Noise tests on the LP2951 are made with a 0.01 μF capacitor connected across Pins 7 and 1.
- 6. Latch-up Current Maximum Rating tested per JEDEC standard: JESD78
  - Inputs Low: passing positive current 100 mA and negative current –100 mA
  - Inputs High: passing positive current 100 mA and negative current -10 mA.

\*NCV prefix is for automotive and other applications requiring site and change control.

#### **ELECTRICAL CHARACTERISTICS** (continued)

(V<sub>in</sub> = V<sub>O</sub> + 1.0 V, I<sub>O</sub> = 100  $\mu$ A, C<sub>O</sub> = 1.0  $\mu$ F, T<sub>A</sub> = 25  $^{\circ}$ C [Note 9], unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Line Regulation (V <sub>in</sub> = V <sub>O(nom)</sub> +1.0 V to 30 V) (Note 10)	Reg <sub>line</sub>				%
LP2950C-XX/LP2951C/LP2951C-XX/NCV2951C*		-	0.08	0.20	
LP2950AC-XX/LP2951AC/LP2951AC-XX/NCV2951AC*	D	-	0.04	0.10	0/
Load Regulation (I <sub>O</sub> = 100 μA to 100 mA) LP2950C-XX/LP2951C/LP2951C-XX/NCV2951C*	Reg <sub>load</sub>	_	0.13	0.20	%
LP2950AC-XX/LP2951AC/LP2951AC-XX/NCV2951AC*		_	0.05	0.10	
Dropout Voltage	$V_I - V_O$				mV
$I_O = 100 \mu A$		-	30	80	
I <sub>O</sub> = 100 mA		-	350	450	
Supply Bias Current	I <sub>CC</sub>		00	100	
$I_{O} = 100 \mu A$ $I_{O} = 100 \text{ mA}$		_	93 4.0	120 12	μA mA
Dropout Supply Bias Current (V <sub>in</sub> = V <sub>O(nom)</sub> – 0.5 V,	I <sub>CCdropout</sub>	_	110	170	μΑ
$I_0 = 100 \mu\text{A}$ ) (Note 10)	Codropout				μυτ
Current Limit (V <sub>O</sub> Shorted to Ground)	l <sub>Limit</sub>	-	220	300	mA
Thermal Regulation	Reg <sub>thermal</sub>	-	0.05	0.20	%/W
Output Noise Voltage (10 Hz to 100 kHz) (Note 11)	V <sub>n</sub>				μVrms
$C_L = 1.0 \mu\text{F}$		-	126	-	
C <sub>L</sub> = 100 μF		_	56	_	
LP2951A/LP2951AC Only					
Reference Voltage (T <sub>A</sub> = 25°C) LP2951C/LP2951C-XX/NCV2951C*	$V_{ref}$	1.210	1.235	1.260	V
LP2951AC/LP2951AC-XX/NCV2951AC*		1.220	1.235	1.250	
Reference Voltage (T <sub>A</sub> = -40 to +125°C)	V <sub>ref</sub>				V
LP2951C/LP2951C-XX/NCV2951C*	101	1.200	-	1.270	
LP2951AC/LP2951AC-XX/NCV2951AC*		1.200	-	1.260	
Reference Voltage ( $T_A = -40 \text{ to } +125^{\circ}\text{C}$ )	$V_{ref}$				V
I <sub>O</sub> = 100 μA to 100 mA, V <sub>in</sub> = 23 to 30 V LP2951C/LP2951C-XX/NCV2951C*		1.185		1.285	
LP2951AC/LP2951AC-XX/NCV2951AC*		1.190	_	1.270	
Feedback Pin Bias Current	I <sub>FB</sub>	-	15	40	nA
Error Comparator	•			•	
Output Leakage Current (V <sub>OH</sub> = 30 V)	I <sub>lkg</sub>	-	0.01	1.0	μΑ
Output Low Voltage (V <sub>in</sub> = 4.5 V, I <sub>OL</sub> = 400 μA)	V <sub>OL</sub>	-	150	250	mV
Upper Threshold Voltage (V <sub>in</sub> = 6.0 V)	$V_{thu}$	40	45	-	mV
Lower Threshold Voltage (V <sub>in</sub> = 6.0 V)	$V_{thl}$	-	60	95	mV
Hysteresis (V <sub>in</sub> = 6.0 V)	$V_{hy}$	-	15	-	mV
Shutdown Input					
Input Logic Voltage	V <sub>shtdn</sub>				V
Logic "0" (Regulator "On")		0	-	0.7	
Logic "1" (Regulator "Off")	1	2.0	-	30	
Shutdown Pin Input Current V <sub>shtdn</sub> = 2.4 V	l <sub>shtdn</sub>	_	35	50	μΑ
$V_{\text{Shtdn}} = 2.4 \text{ V}$ $V_{\text{Shtdn}} = 30 \text{ V}$		_	450	600	
Regulator Output Current in Shutdown Mode	I <sub>off</sub>	-	3.0	10	μΑ
(V <sub>in</sub> = 30 V, V <sub>shtdn</sub> = 2.0 V, V <sub>O</sub> = 0, Pin 6 Connected to Pin 7)  Product parametric performance is indicated in the Electrical Chair					

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>7.</sup> The Junction-to-Ambient Thermal Resistance is determined by PCB copper area per Figure 29.

<sup>8.</sup> ESD data available upon request.

<sup>9.</sup> Low duty pulse techniques are used during test to maintain junction temperature as close to ambient as possible.

<sup>10.</sup>  $V_{O(nom)}$  is the part number voltage option. 11. Noise tests on the LP2951 are made with a 0.01  $\mu$ F capacitor connected across Pins 7 and 1.

<sup>\*</sup>NCV prefix is for automotive and other applications requiring site and change control.

#### **DEFINITIONS**

**Dropout Voltage** – The input/output voltage differential at which the regulator output no longer maintains regulation against further reductions in input voltage. Measured when the output drops 100 mV below its nominal value (which is measured at 1.0 V differential), dropout voltage is affected by junction temperature, load current and minimum input supply requirements.

**Line Regulation** – The change in output voltage for a change in input voltage. The measurement is made under conditions of low dissipation or by using pulse techniques such that average chip temperature is not significantly affected.

**Load Regulation** – The change in output voltage for a change in load current at constant chip temperature.

**Maximum Power Dissipation** – The maximum total device dissipation for which the regulator will operate within specifications.

**Bias Current** – Current which is used to operate the regulator chip and is not delivered to the load.

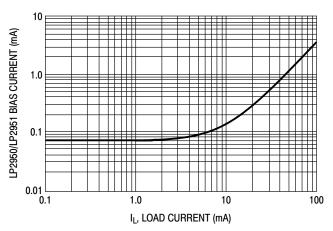


Figure 2. Quiescent Current

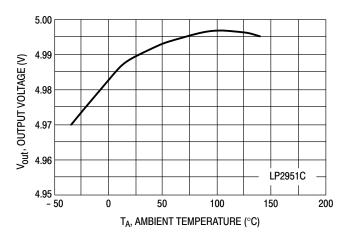


Figure 4. Output Voltage versus Temperature

**Output Noise Voltage** – The RMS ac voltage at the output, with constant load and no input ripple, measured over a specified frequency range.

**Leakage Current** – Current drawn through a bipolar transistor collector–base junction, under a specified collector voltage, when the transistor is "off".

**Upper Threshold Voltage** – Voltage applied to the comparator input terminal, below the reference voltage which is applied to the other comparator input terminal, which causes the comparator output to change state from a logic "0" to "1".

**Lower Threshold Voltage** – Voltage applied to the comparator input terminal, below the reference voltage which is applied to the other comparator input terminal, which causes the comparator output to change state from a logic "1" to "0".

**Hysteresis** – The difference between Lower Threshold voltage and Upper Threshold voltage.

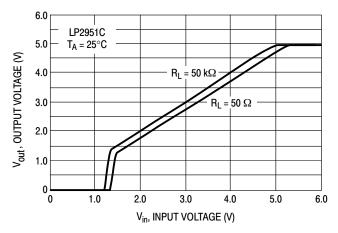


Figure 3. 5.0 V Dropout Characteristics over Load

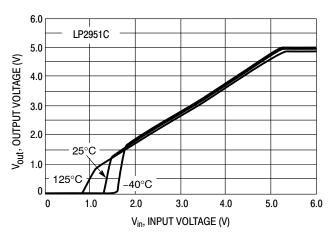


Figure 5. 5.0 V Dropout Characteristics with  $$R_L=50~\Omega$$ 

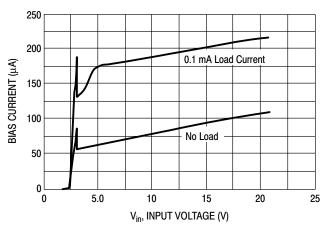


Figure 6. Input Current

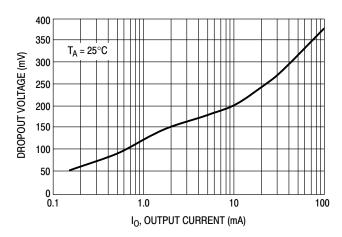


Figure 7. Dropout Voltage versus Output Current

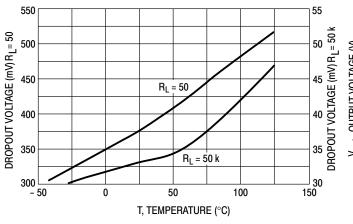


Figure 8. Dropout Voltage versus Temperature

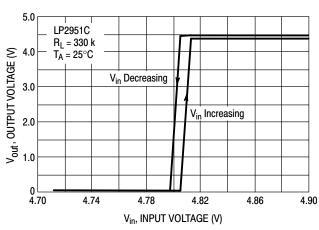


Figure 9. Error Comparator Output

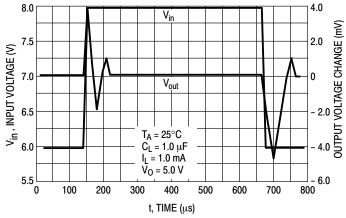


Figure 10. Line Transient Response

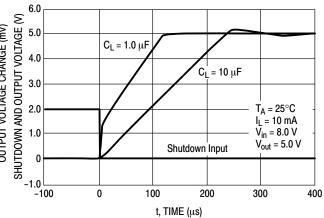


Figure 11. LP2951 Enable Transient

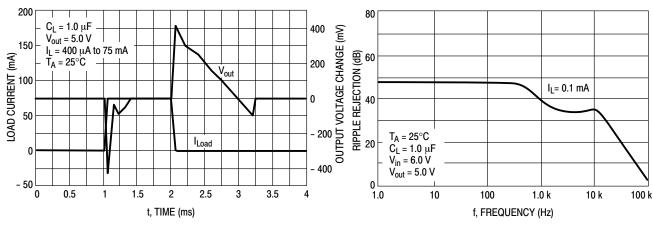


Figure 12. Load Transient Response

Figure 13. Ripple Rejection

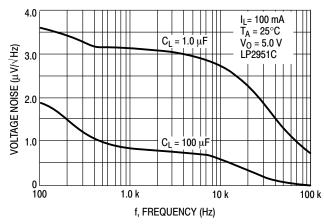


Figure 14. Output Noise

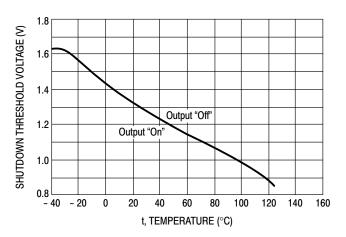


Figure 15. Shutdown Threshold Voltage versus Temperature

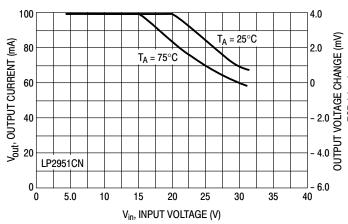


Figure 16. Maximum Rated Output Current

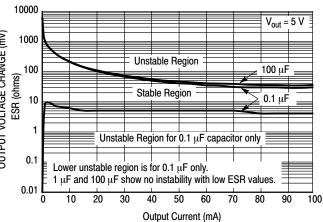


Figure 17. Output Stability versus Output Capacitor Change

#### **APPLICATIONS INFORMATION**

#### Introduction

The LP2950/LP2951 regulators are designed with internal current limiting and thermal shutdown making them user-friendly. Typical application circuits for the LP2950 and LP2951 are shown in Figures 20 through 28.

These regulators are not internally compensated and thus require a 1.0  $\mu F$  (or greater) capacitance between the LP2950/LP2951 output terminal and ground for stability. Most types of aluminum, tantalum or multilayer ceramic will perform adequately. Solid tantalums or appropriate multilayer ceramic capacitors are recommended for operation below 25°C.

At lower values of output current, less output capacitance is required for output stability. The capacitor can be reduced to  $0.33\,\mu F$  for currents less than 10 mA, or  $0.1\,\mu F$  for currents below 1.0 mA. Using the 8 pin versions at voltages less than 5.0 V operates the error amplifier at lower values of gain, so that more output capacitance is needed for stability. For the worst case operating condition of a 100 mA load at 1.23 V output (output Pin 1 connected to the feedback Pin 7) a minimum capacitance of  $3.3\,\mu F$  is recommended.

The LP2950 will remain stable and in regulation when operated with no output load. When setting the output voltage of the LP2951 with external resistors, the resistance values should be chosen to draw a minimum of  $1.0~\mu A$ .

A bypass capacitor is recommended across the LP2950/LP2951 input to ground if more than 4 inches of wire connects the input to either a battery or power supply filter capacitor.

Input capacitance at the LP2951 Feedback Pin 7 can create a pole, causing instability if high value external resistors are used to set the output voltage. Adding a 100 pF capacitor between the Output Pin 1 and the Feedback Pin 7 and increasing the output filter capacitor to at least 3.3  $\mu F$  will stabilize the feedback loop.

#### **Error Detection Comparator**

The comparator switches to a positive logic low whenever the LP2951 output voltage falls more than approximately 5.0% out of regulation. This value is the comparator's designed–in offset voltage of 60 mV divided by the 1.235 V internal reference. As shown in the representative block diagram. This trip level remains 5.0% below normal regardless of the value of regulated output voltage. For example, the error flag trip level is 4.75 V for a normal 5.0 V regulated output, or 9.50 V for a 10 V output voltage.

Figure 2 is a timing diagram which shows the  $\overline{ERROR}$  signal and the regulated output voltage as the input voltage

to the LP2951 is ramped up and down. The ERROR signal becomes valid (low) at about 1.3 V input. It goes high when the input reaches about 5.0 V (Vout exceeds about 4.75 V). Since the LP2951's dropout voltage is dependent upon the load current (refer to the curve in the Typical Performance Characteristics), the input voltage trip point will vary with load current. The output voltage trip point does not vary with load.

The error comparator output is an open collector which requires an external pullup resistor. This resistor may be returned to the output or some other voltage within the system. The resistance value should be chosen to be consistent with the 400  $\mu A$  sink capability of the error comparator. A value between 100 k $\Omega$  and 1.0 M $\Omega$  is suggested. No pullup resistance is required if this output is unused.

When operated in the power down mode ( $V_{in}=0\ V$ ), the error comparator output will go high if it has been pulled up to an external supply (the output transistor is in high impedance state). To avoid this invalid response, the error comparator output should be pulled up to  $V_{out}$  (see Figure 18).

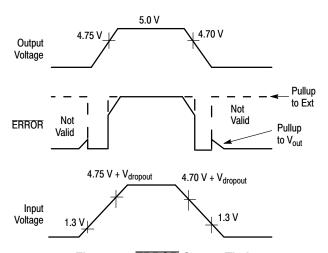


Figure 18. ERROR Output Timing

#### **Programming the Output Voltage (LP2951)**

The LP2951CX may be pin-strapped for the nominal fixed output voltage using its internal voltage divider by tying Pin 1 (output) to Pin 2 (sense) and Pin 7 (feedback) to Pin 6 (5.0 V tap). Alternatively, it may be programmed for any output voltage between its 1.235 reference voltage and its 30 V maximum rating. An external pair of resistors is required, as shown in Figure 19.

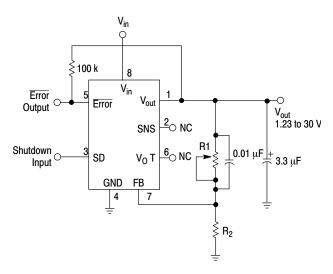


Figure 19. Adjustable Regulator

The complete equation for the output voltage is:

$$V_{out} = V_{ref} (1 + R1/R2) + I_{FB} R1$$

where  $V_{ref}$  is the nominal 1.235 V reference voltage and  $I_{FB}$  is the feedback pin bias current, nominally -20 nA. The minimum recommended load current of 1.0  $\mu$ A forces an upper limit of 1.2 M $\Omega$  on the value of R2, if the regulator must work with no load.  $I_{FB}$  will produce a 2% typical error in  $V_{out}$  which may be eliminated at room temperature by adjusting R1. For better accuracy, choosing R2 = 100 k reduces this error to 0.17% while increasing the resistor program current to 12  $\mu$ A. Since the LP2951 typically draws 75  $\mu$ A at no load with Pin 2 open circuited, the extra 12  $\mu$ A of current drawn is often a worthwhile tradeoff for eliminating the need to set output voltage in test.

## **Output Noise**

In many applications it is desirable to reduce the noise present at the output. Reducing the regulator bandwidth by increasing the size of the output capacitor is the only method for reducing noise on the 3 lead LP2950. However, increasing the capacitor from 1.0  $\mu F$  to 220  $\mu F$  only decreases the noise from 430  $\mu V$  to 160  $\mu V rms$  for a 100 kHz bandwidth at the 5.0 V output.

Noise can be reduced fourfold by a bypass capacitor across R1, since it reduces the high frequency gain from 4 to unity. Pick

$$C_{Bypass} \approx \frac{1}{2\pi R1 \times 200 \text{ Hz}}$$

or about 0.01  $\mu$ F. When doing this, the output capacitor must be increased to 3.3  $\mu$ F to maintain stability. These changes reduce the output noise from 430  $\mu$ V to 126  $\mu$ Vrms for a 100 kHz bandwidth at 5.0 V output. With bypass capacitor added, noise no longer scales with output voltage so that improvements are more dramatic at higher output voltages.

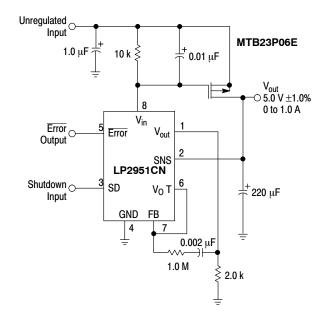


Figure 20. 1.0 A Regulator with 1.2 V Dropout

#### **TYPICAL APPLICATIONS**

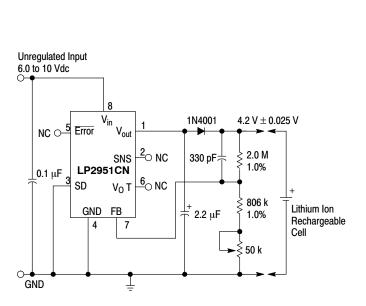


Figure 21. Lithium Ion Battery Cell Charger

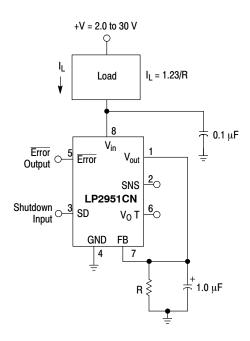


Figure 22. Low Drift Current Sink

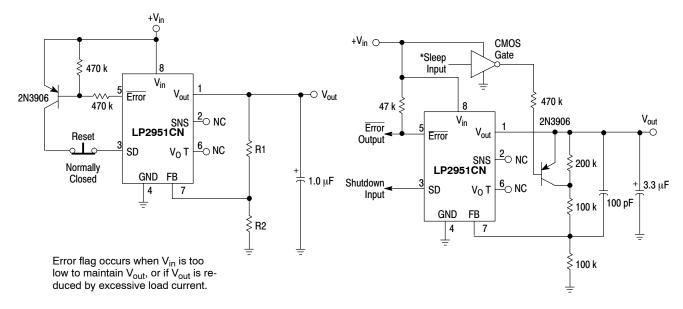
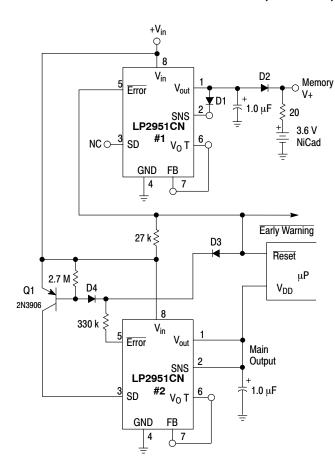


Figure 23. Latch Off When Error Flag Occurs

Figure 24. 5.0 V Regulator with 2.5 V Sleep Function



All diodes are 1N4148.

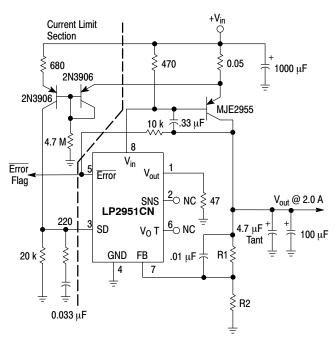
Early Warning flag on low input voltage.

Main output latches off at lower input voltages.

Battery backup on auxiliary output.

Operation: Regulator #1's  $V_{out}$  is programmed one diode drop above 5.0 V. Its error flag becomes active when  $V_{in} \leq 5.7$  V. When  $V_{in}$  drops below 5.3 V, the error flag of regulator #2 becomes active and via Q1 latches the main output "off". When  $V_{in}$  again exceeds 5.7 V, regulator #1 is back in regulation and the early warning signal rises, unlatching regulator #2 via D3.

Figure 25. Regulator with Early Warning and Auxiliary Output



 $V_{out} = 1.25V (1.0 + R1/R2)$ 

For 5.0 V output, use internal resistors. Wire Pin 6 to 7, and wire Pin 2 to +V  $_{\rm out}$  Bus.

Figure 26. 2.0 A Low Dropout Regulator

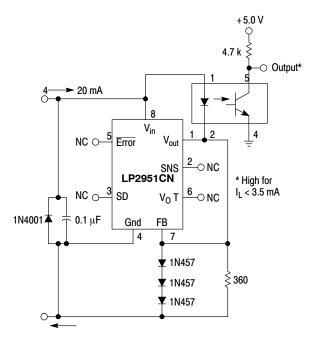


Figure 27. Open Circuit Detector for 4.0 to 20 mA Current Loop

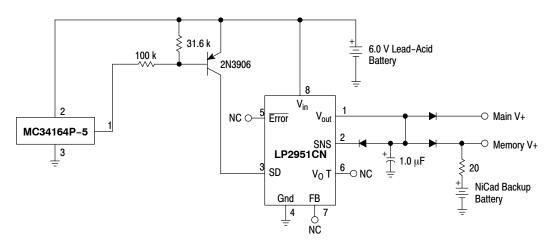


Figure 28. Low Battery Disconnect

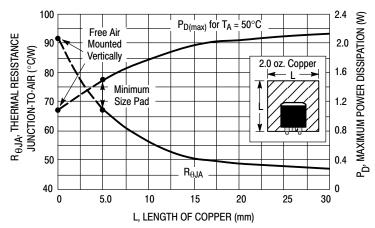


Figure 29. DPAK Thermal Resistance and Maximum Power Dissipation versus PCB Copper Length

# **ORDERING INFORMATION (LP2950)**

Part Number	Output Voltage (Volts)	Tolerance (%)	Package	Shipping <sup>†</sup>
LP2950CZ-3.0G	3.0	1.0	TO-92 (Pb-Free)	2000 Units / Bag
LP2950CZ-3.0RAG	50CZ-3.0RAG 3.0		TO-92 (Pb-Free)	2000 Units / Tape & Reel
LP2950ACZ-3.0G	3.0	0.5	TO-92 (Pb-Free)	2000 Units / Bag
LP2950ACZ-3.0RAG	3.0	0.5	TO-92 (Pb-Free)	2000 Units / Tape & Reel
LP2950CZ-3.3G	3.3	1.0	TO-92 (Pb-Free)	2000 Units / Bag
LP2950CZ-3.3RAG	3.3	1.0	TO-92 (Pb-Free)	2000 Units / Tape & Reel
LP2950ACZ-3.3G	3.3	0.5	TO-92 (Pb-Free)	2000 Units / Bag
LP2950ACZ-3.3RAG	3.3	0.5	TO-92 (Pb-Free)	2000 Units / Tape & Reel
LP2950CZ-5.0G	5.0	1.0	TO-92 (Pb-Free)	2000 Units / Bag
LP2950CZ-5.0RAG	5.0	1.0	TO-92 (Pb-Free)	2000 Units / Tape & Reel
LP2950CZ-5.0RPG	5.0	1.0	TO-92 (Pb-Free)	2000 Units / Ammo Pack
LP2950ACZ-5.0G	5.0	0.5	TO-92 (Pb-Free)	2000 Units / Bag
LP2950ACZ-5.0RAG	5.0	0.5	TO-92 (Pb-Free)	2000 Units / Tape & Reel
LP2950CDT-3.0RKG	3.0	1.0	DPAK (Pb-Free)	2500 Units / Tape & Reel
LP2950CDT-3.3G	3.3	1.0	DPAK (Pb-Free)	75 Units / Rail
LP2950CDT-3.3RKG	3.3	1.0	DPAK (Pb-Free)	2500 Units / Tape & Reel
LP2950ACDT-3.3RG	3.3	0.5	DPAK (Pb-Free)	2500 Units / Tape & Reel
LP2950CDT-5.0G	5.0	1.0	DPAK (Pb-Free)	75 Units / Rail
LP2950CDT-5.0RKG	5.0	1.0	DPAK (Pb-Free)	2500 Units / Tape & Reel
LP2950ACDT-5.0G	5.0	0.5	DPAK (Pb-Free)	75 Units / Rail
LP2950ACDT-5RKG	5.0	0.5	DPAK (Pb-Free)	2500 Units / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# **ORDERING INFORMATION (LP2951)**

Part Number	Output Voltage (Volts)	Tolerance (%)	Package	Shipping <sup>†</sup>
LP2951CD-3.0R2G	3.0	1.0	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
LP2951ACD-3.0R2G	3.0	0.5	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
LP2951CD-3.3R2G	3.3	1.0	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
LP2951ACD-3.3G	3.3	0.5	SOIC-8 (Pb-Free)	98 Units / Rail
LP2951ACD-3.3R2G	3.3	0.5	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
LP2951CDG	51CDG 5.0 or Adj.		SOIC-8 (Pb-Free)	98 Units / Rail
LP2951CDR2G	5.0 or Adj.	1.0	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
LP2951ACDG	5.0 or Adj.	0.5	SOIC-8 (Pb-Free)	98 Units / Rail
LP2951ACDR2G	5.0 or Adj.	0.5	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
LP2951ACDM-3.0RG	3.0	0.5	Micro8 (Pb-Free)	4000 Units / Tape & Reel
LP2951ACDM-3.3RG	3.3	0.5	Micro8 (Pb-Free)	4000 Units / Tape & Reel
LP2951CDMR2G	5.0 or Adj.	1.0	Micro8 (Pb-Free)	4000 Units / Tape & Reel
LP2951ACDMR2G	5.0 or Adj.	0.5	Micro8 (Pb-Free)	4000 Units / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

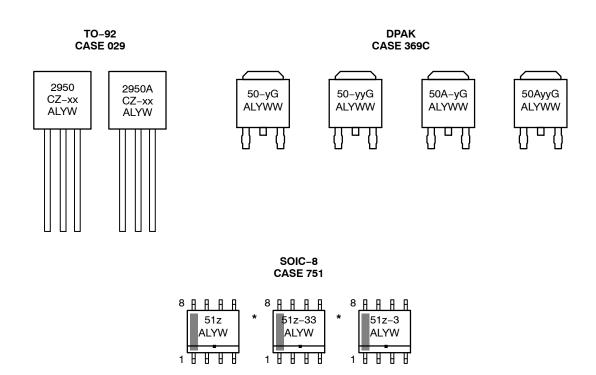
# **ORDERING INFORMATION (NCV2951)**

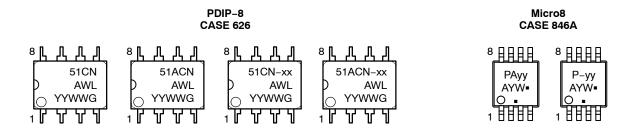
Part Number	Output Voltage (Volts)	Tolerance (%)	Package	Shipping <sup>†</sup>
NCV2951ACD3.3R2G*	3.3	0.5	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
NCV2951ACDR2G*	5.0 or Adj.	0.5	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
NCV2951CDR2G*	5.0 or Adj.	1.0	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel
NCV2951ACDMR2G*	5.0 or Adj.	0.5	Micro8 (Pb-Free)	4000 Units / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

### **MARKING DIAGRAMS**





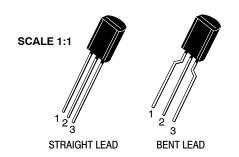
xx = 3.0, 3.3, or 5.0 y = 3 or 5 yy = 30, 33, or 50 z = A or C

A = Assembly Location WL, L = Wafer Lot

YY, Y = Year WW, W = Work Week G = Pb-Free Package ■ Pb-Free Package

(Note: Microdot may be in either location)

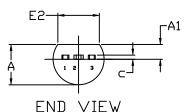
<sup>\*</sup>This marking diagram also applies to NCV2951.

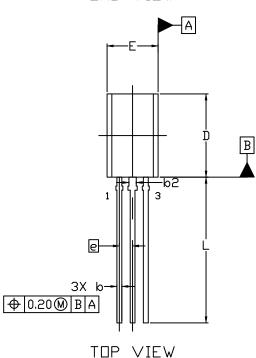


TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

**DATE 05 MAR 2021** 

### STRAIGHT LEAD





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS					
DIM	MIN.	N□M.	MAX.			
Δ	3.75	3.90	4.05			
A1	1.28	1.43	1.58			
Ø	0.38	0.465	0.55			
ρQ	0.62	0.70	0.78			
C	0.35	0.40	0.45			
D	7.85	8.00	8.15			
E	4.75	4.90	5.05			
E2	3.90					
е	1.27 BSC					
L	13.80	14.00	14.20			

## STYLES AND MARKING ON PAGE 3

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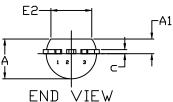
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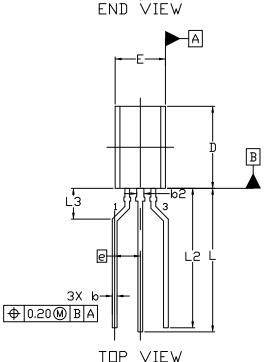


TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

**DATE 05 MAR 2021** 

### FORMED LEAD





#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
- 4. DIMENSION 6 AND 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION 62 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS					
DIM	MIN.	N□M.	MAX.			
Α	3.75	3.90	4.05			
A1	1.28	1.43	1.58			
b	0.38	0.465	0.55			
b2	0.62	0.70	0.78			
С	0.35	0.40	0.45			
D	7.85	8.00	8.15			
Е	4.75	4.90	5.05			
E2	3.90					
O.	2.50 BSC					
L	13.80	14.00	14.20			
L2	13.20	13.60	14.00			
L3	3.00 REF					

## STYLES AND MARKING ON PAGE 3

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# TO-92 (TO-226) 1 WATT

CASE 29-10 ISSUE D

### **DATE 05 MAR 2021**

2.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	PIN 1. 2.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	
	GATE	PIN 1.	SOURCE DRAIN	PIN 1. 2.	DRAIN	2.	BASE 1 EMITTER BASE 2		CATHODE GATE ANODE
2.	CATHODE & ANODE	2.	MAIN TERMINAL 1 GATE MAIN TERMINAL 2	2.	ANODE 1 GATE CATHODE 2		EMITTER COLLECTOR BASE	STYLE 15: PIN 1. 2. 3.	ANODE 1
2.	ANODE	DINI 1	COLLECTOR BASE EMITTER	PIN 1	ANODE	PIN 1. 2.	GATE ANODE CATHODE	2.	NOT CONNECTED CATHODE ANODE
2.		PIN 1. 2.		PIN 1. 2.	GATE	PIN 1. 2.	EMITTER COLLECTOR/ANODE CATHODE	PIN 1. 2.	MT 1
	V <sub>CC</sub>		MT	PIN 1. 2.		PIN 1. 2.	NOT CONNECTED ANODE CATHODE	PIN 1. 2.	
		STYLE 32: PIN 1. 2. 3.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN	PIN 1. 2.	INPUT GROUND LOGIC		

# GENERIC MARKING DIAGRAM\*



XXXX = Specific Device Code

A = Assembly Location

L = Wafer Lot Y = Year

W = Work Week

= Pb-Free Package

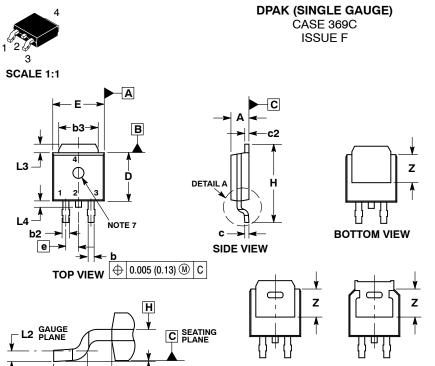
(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	TO-92 (TO-226) 1 WATT		PAGE 3 OF 3

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**DATE 21 JUL 2015** 



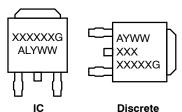
#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
   CONTROLLING DIMENSION: INCHES.
- 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-
- MENSIONS b3, L3 and Z.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
  5. DIMENSIONS D AND E ARE DETERMINED AT THE
- OUTERMOST EXTREMES OF THE PLASTIC BODY.

  6. DATUMS A AND B ARE DETERMINED AT DATUM
- 7. OPTIONAL MOLD FEATURE.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
С	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
е	0.090 BSC		2.29 BSC	
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020 BSC		0.51	BSC
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	

#### **GENERIC MARKING DIAGRAM\***



XXXXXX = Device Code

= Assembly Location Α

L = Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking.

# **SOLDERING FOOTPRINT\***

STYLE 8:

STYLE 3:

PIN 1. N/C 2. CATHODE

3. ANODE 4. CATHODE

PIN 1. ANODE 2. CATHODE

3. ANODE

4. CATHODE

STYLE 9:

PIN 1. ANODE 2. CATHODE

Α1

STYLE 2:

PIN 1. GATE 2. COLLECTOR

3. EMITTER 4. COLLECTOR

PIN 1. GATE 2. DRAIN

SOURCE

4. DRAIN

**DETAIL A** ROTATED 90° CW

STYLE 7:

STYLE 1:

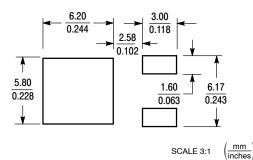
STYLE 6:

PIN 1. MT1 2. MT2

3. GATE 4. MT2

PIN 1. BASE 2. COLLECTOR 3. EMITTER

4. COLLECTOR



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1

**BOTTOM VIEW** 

ALTERNATE CONSTRUCTIONS

STYLE 5:

STYLE 10:

PIN 1. GATE 2. ANODE 3. CATHODE

4. ANODE

PIN 1. CATHODE 2. ANODE

3. CATHODE 4. ANODE

STYLE 4:

PIN 1. CATHODE 2. ANODE 3. GATE

4. ANODE

3. RESISTOR ADJUST 4. CATHODE

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PDIP-8 CASE 626-05 ISSUE P

**DATE 22 APR 2015** 



**TOP VIEW** 

b2

В



NOTE 5

e/2 NOTE 3 SEATING PLANE C D1 eВ 8X b **END VIEW** |⊕|0.010 M| C| A M| B M NOTE 6 SIDE VIEW

STYLE 1: PIN 1. AC IN 2. DC + IN 3. DC - IN 4. AC IN 5. GROUND 6. OUTPUT 7. AUXILIARY 8. V<sub>CC</sub>

#### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: INCHES.
  DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACK-
- AGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
  DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
- DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR
- 6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE
- LEADS UNCONSTRAINED.

  DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
- PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α		0.210		5.33
A1	0.015		0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060 TYP		1.52 TYP	
С	0.008	0.014	0.20	0.36
D	0.355	0.400	9.02	10.16
D1	0.005		0.13	
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
е	0.100 BSC		2.54	BSC
eВ		0.430		10.92
L	0.115	0.150	2.92	3.81
М		10°		10°

# **GENERIC MARKING DIAGRAM\***



XXXX = Specific Device Code = Assembly Location

WL = Wafer Lot YY = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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SOIC-8 NB CASE 751-07 **ISSUE AK** 

**DATE 16 FEB 2011** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		ERS INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
М	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

#### **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location

= Wafer Lot = Year = Work Week

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

#### **STYLES ON PAGE 2**

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# SOIC-8 NB CASE 751-07 ISSUE AK

# DATE 16 FEB 2011

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1  STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE  STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. PINS 2	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1  STYLE 7: PIN 1. IMPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2	3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1  STYLE 12: PIN 1. SOURCE 2. SOURCE
PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND	PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd  STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2	PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1  STYLE 12: PIN 1. SOURCE 2. SOURCE
PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND	PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2	PIN 1. SOURCE 2. SOURCE
6. BIAS 2 7. INPUT 8. GROUND	5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15:  PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		
	PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE 8. CATHODE 8. CATHODE 8. CATHODE 8. CATHODE 9. COMMON CATHODE/VCC 9. COMMON CATHODE/VCC 1. I/O LINE 1 2. COMMON CATHODE/VCC 1. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 5 8. COMMON ANODE/GND 8. COMMON ANODE/GND 8. COMMON ANODE/GND 8. COMMON ANODE/GND 8. I/O LINE 5 8. COMMON ANODE/GND 8. SOURCE 9. I/O LINE 5 8. COMMON ANODE/GND 8. VILLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILLIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC 8. VCC 8. VCC 8. VCC 8. VCC 8. SOURCE 2 4. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2	PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. N-DRAIN 8. CATHODE, COMMON 8. N-DRAIN 8. CATHODE, COMMON 8. CATHODE 9IN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 4. GATE 2 5. DRAIN 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1 8. COMMON CATHODE/VCC 1. COMMON CATHODE/VCC 1. COMMON CATHODE/VCC 1. (/O LINE 1 2. COMMON CATHODE/VCC 1. (/O LINE 3 5. COMMON ANODE/GND 6. (/O LINE 4 7. (/O LINE 5 8. COMMON ANODE/GND 8. LINE 2 OUT 9. COMMON ANODE/GND 8. LINE 1 OUT  STYLE 26: PIN 1. GND 9. LINE 2 OUT 9. COMMON ANODE/GND 9. LINE 1 OUT  STYLE 27: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 1 OUT  STYLE 28: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 1 OUT  STYLE 29: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 1 OUT  STYLE 29: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 2 OUT 9. COMMON ANODE/GND 9. LINE 1 OUT  STYLE 29: PIN 1. ILIMIT 9. COMMON ANODE/GND 9. LINE 1 OUT  STYLE 29: PIN 1. ILIMIT 9. SOURCE 1/DRAIN 2

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#### Micro8 CASE 846A-02 ISSUE K

**DATE 16 JUL 2020** 









#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
- DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
- A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



MOUNTING FOOTPRINT

DIM	MI	LLIMETE	RS
ואזמ	MIN.	N□M.	MAX.
Α	-	-	1.10
A1	0.05	0.08	0.15
b	0.25	0.33	0.40
c	0.13	0.18	0.23
D	2.90	3.00	3.10
Ε	2.90	3.00	3.10
е	0.65 BSC		
HE	4.75	4.90	5.05
L	0.40	0.55	0.70

### **GENERIC MARKING DIAGRAM\***



XXXX = Specific Device Code Α = Assembly Location

Υ = Year W = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. SOURCE	PIN 1. SOURCE 1	PIN 1. N-SOURCE
<ol><li>SOURCE</li></ol>	2. GATE 1	2. N-GATE
<ol><li>SOURCE</li></ol>	3. SOURCE 2	<ol><li>P-SOURCE</li></ol>
<ol><li>GATE</li></ol>	4. GATE 2	4. P-GATE
<ol><li>DRAIN</li></ol>	5. DRAIN 2	5. P-DRAIN
<ol><li>DRAIN</li></ol>	6. DRAIN 2	6. P-DRAIN
7. DRAIN	7. DRAIN 1	7. N-DRAIN
8. DRAIN	8. DRAIN 1	8. N-DRAIN

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